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Kind regards,

Team Nexperia

74AUP1G125

Low-power buffer/line driver; 3-state

Rev. 6 — 15 August 2012

Product data sheet

1. General description

The 74AUP1G125 provides a single non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input ($\overline{OE}$). A HIGH level at pin $\overline{OE}$ causes the output to assume a high-impedance OFF-state. This device has the input-disable feature, which allows floating input signals. The inputs are disabled when the output enable input ($\overline{OE}$) is HIGH.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V. This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114F Class 3A exceeds 5000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot $< 10\%$ of V_{CC}
- Input-disable feature allows floating input conditions
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$



3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AUP1G125GW	−40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74AUP1G125GM	−40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886
74AUP1G125GF	−40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891
74AUP1G125GN	−40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 0.9 × 1.0 × 0.35 mm	SOT1115
74AUP1G125GS	−40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 × 1.0 × 0.35 mm	SOT1202
74AUP1G125GX	−40 °C to +125 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body 0.8 × 0.8 × 0.35 mm	SOT1226

4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74AUP1G125GW	pM
74AUP1G125GM	pM
74AUP1G125GF	pM
74AUP1G125GN	pM
74AUP1G125GS	pM
74AUP1G125GX	pM

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

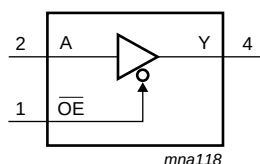


Fig 1. Logic symbol

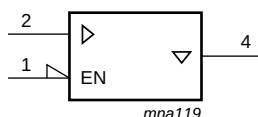


Fig 2. IEC logic symbol

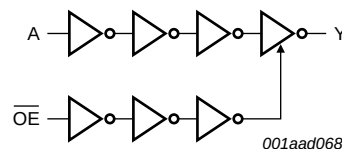


Fig 3. Logic diagram

6. Pinning information

6.1 Pinning

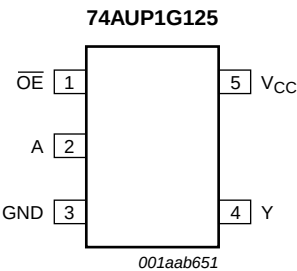


Fig 4. Pin configuration SOT353-1

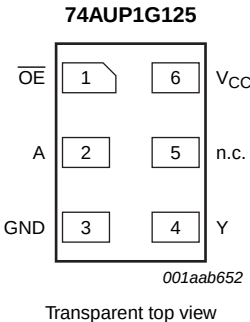


Fig 5. Pin configuration SOT886

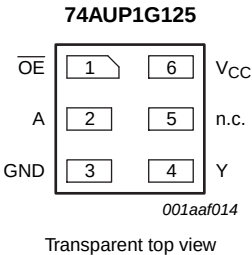


Fig 6. Pin configuration SOT891, SOT1115 and SOT1202

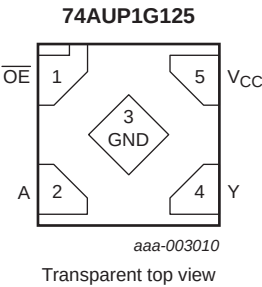


Fig 7. Pin configuration SOT1226 (X2SON5)

6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	TSSOP5 and X2SON5	XSON6	
$\overline{\text{OE}}$	1	1	output enable input
A	2	2	data input
GND	3	3	ground (0 V)
Y	4	4	data output
n.c.	-	5	not connected
V _{CC}	5	6	supply voltage

7. Functional description

Table 4. Function table^[1]

Input		Output
OE	A	Y
L	L	L
L	H	H
H	X	Z

- [1] H = HIGH voltage level;
 L = LOW voltage level;
 X = Don't care;
 Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
I_{IK}	input clamping current	$V_I < 0$ V	-50	-	mA
V_I	input voltage		^[1] -0.5	+4.6	V
I_{OK}	output clamping current	$V_O < 0$ V	-50	-	mA
V_O	output voltage	Active mode	^[1] -0.5	$V_{CC} + 0.5$	V
		Power-down mode	^[1] -0.5	+4.6	V
I_O	output current	$V_O = 0$ V to V_{CC}	-	±20	mA
I_{CC}	supply current		-	+50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	^[2] -	250	mW

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 [2] For TSSOP5 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.
 For XSON6 and X2SON5 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		0.8	3.6	V
V_I	input voltage		0	3.6	V
V_O	output voltage	Active mode	0	V_{CC}	V
		Power-down mode; $V_{CC} = 0$ V	0	3.6	V
T_{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 0.8$ V to 3.6 V	0	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 µA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.75 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.11	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.32	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	2.05	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.9	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.72	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.6	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 µA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.31	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.44	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.1	µA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = 0 V to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.1	µA
I _{OFF}	power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±0.2	µA
ΔI _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.2	µA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.5	µA

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
ΔI_{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6\text{ V}$; $I_O = 0\text{ A}$; $V_{CC} = 3.3\text{ V}$	[1]	-	-	40 μA
		$\overline{OE}$ input; $V_I = V_{CC} - 0.6\text{ V}$; $I_O = 0\text{ A}$; $V_{CC} = 3.3\text{ V}$	[1]	-	-	110 μA
		all inputs; $V_I = \text{GND to } 3.6\text{ V}$; $\overline{OE} = V_{CC}$; $V_{CC} = 0.8\text{ V to } 3.6\text{ V}$	[2]	-	-	1 μA
C_I	input capacitance	$V_{CC} = 0\text{ V to } 3.6\text{ V}$; $V_I = \text{GND or } V_{CC}$	-	0.9	-	pF
C_O	output capacitance					
	output enabled	$V_O = \text{GND}$; $V_{CC} = 0\text{ V}$	-	1.7	-	pF
	output disabled	$V_{CC} = 0\text{ V to } 3.6\text{ V}$; $V_O = \text{GND or } V_{CC}$	-	1.5	-	pF
$T_{\text{amb}} = -40\text{ }^{\circ}\text{C to } +85\text{ }^{\circ}\text{C}$						
V_{IH}	HIGH-level input voltage	$V_{CC} = 0.8\text{ V}$	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9\text{ V to } 1.95\text{ V}$	$0.65 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3\text{ V to } 2.7\text{ V}$	1.6	-	-	V
		$V_{CC} = 3.0\text{ V to } 3.6\text{ V}$	2.0	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 0.8\text{ V}$	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9\text{ V to } 1.95\text{ V}$	-	-	$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3\text{ V to } 2.7\text{ V}$	-	-	0.7	V
		$V_{CC} = 3.0\text{ V to } 3.6\text{ V}$	-	-	0.9	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}\text{ or } V_{IL}$				
		$I_O = -20\text{ }\mu\text{A}$; $V_{CC} = 0.8\text{ V to } 3.6\text{ V}$	$V_{CC} - 0.1$	-	-	V
		$I_O = -1.1\text{ mA}$; $V_{CC} = 1.1\text{ V}$	$0.7 \times V_{CC}$	-	-	V
		$I_O = -1.7\text{ mA}$; $V_{CC} = 1.4\text{ V}$	1.03	-	-	V
		$I_O = -1.9\text{ mA}$; $V_{CC} = 1.65\text{ V}$	1.30	-	-	V
		$I_O = -2.3\text{ mA}$; $V_{CC} = 2.3\text{ V}$	1.97	-	-	V
		$I_O = -3.1\text{ mA}$; $V_{CC} = 2.3\text{ V}$	1.85	-	-	V
		$I_O = -2.7\text{ mA}$; $V_{CC} = 3.0\text{ V}$	2.67	-	-	V
V_{OL}	LOW-level output voltage	$I_O = -4.0\text{ mA}$; $V_{CC} = 3.0\text{ V}$	2.55	-	-	V
		$V_I = V_{IH}\text{ or } V_{IL}$				
		$I_O = 20\text{ }\mu\text{A}$; $V_{CC} = 0.8\text{ V to } 3.6\text{ V}$	-	-	0.1	V
		$I_O = 1.1\text{ mA}$; $V_{CC} = 1.1\text{ V}$	-	-	$0.3 \times V_{CC}$	V
		$I_O = 1.7\text{ mA}$; $V_{CC} = 1.4\text{ V}$	-	-	0.37	V
		$I_O = 1.9\text{ mA}$; $V_{CC} = 1.65\text{ V}$	-	-	0.35	V
		$I_O = 2.3\text{ mA}$; $V_{CC} = 2.3\text{ V}$	-	-	0.33	V
		$I_O = 3.1\text{ mA}$; $V_{CC} = 2.3\text{ V}$	-	-	0.45	V
I_I	input leakage current	$I_O = 2.7\text{ mA}$; $V_{CC} = 3.0\text{ V}$	-	-	0.33	V
		$I_O = 4.0\text{ mA}$; $V_{CC} = 3.0\text{ V}$	-	-	0.45	V
I_I	input leakage current	$V_I = \text{GND to } 3.6\text{ V}$; $V_{CC} = 0\text{ V to } 3.6\text{ V}$	-	-	± 0.5	μA
I_{OZ}	OFF-state output current	$V_I = V_{IH}\text{ or } V_{IL}$; $V_O = 0\text{ V to } 3.6\text{ V}$; $V_{CC} = 0\text{ V to } 3.6\text{ V}$	-	-	± 0.5	μA
I_{OFF}	power-off leakage current	$V_I\text{ or } V_O = 0\text{ V to } 3.6\text{ V}$; $V_{CC} = 0\text{ V}$	-	-	± 0.5	μA

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
ΔI_{OFF}	additional power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	± 0.6	μ A
I_{CC}	supply current	$V_I = \text{GND}$ or V_{CC} ; $I_O = 0$ A; $V_{CC} = 0.8$ V to 3.6 V	-	-	0.9	μ A
ΔI_{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1] -	-	50	μ A
		$\overline{\text{OE}}$ input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1] -	-	120	μ A
		all inputs; $V_I = \text{GND}$ to 3.6 V; $\text{OE} = V_{CC}$; $V_{CC} = 0.8$ V to 3.6 V	[2] -	-	1	μ A
$T_{\text{amb}} = -40$ °C to $+125$ °C						
V_{IH}	HIGH-level input voltage	$V_{CC} = 0.8$ V	$0.75 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9$ V to 1.95 V	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3$ V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0$ V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 0.8$ V	-	-	$0.25 \times V_{CC}$	V
		$V_{CC} = 0.9$ V to 1.95 V	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 2.3$ V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0$ V to 3.6 V	-	-	0.9	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -20$ μ A; $V_{CC} = 0.8$ V to 3.6 V	$V_{CC} - 0.11$	-	-	V
		$I_O = -1.1$ mA; $V_{CC} = 1.1$ V	$0.6 \times V_{CC}$	-	-	V
		$I_O = -1.7$ mA; $V_{CC} = 1.4$ V	0.93	-	-	V
		$I_O = -1.9$ mA; $V_{CC} = 1.65$ V	1.17	-	-	V
		$I_O = -2.3$ mA; $V_{CC} = 2.3$ V	1.77	-	-	V
		$I_O = -3.1$ mA; $V_{CC} = 2.3$ V	1.67	-	-	V
		$I_O = -2.7$ mA; $V_{CC} = 3.0$ V	2.40	-	-	V
		$I_O = -4.0$ mA; $V_{CC} = 3.0$ V	2.30	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20$ μ A; $V_{CC} = 0.8$ V to 3.6 V	-	-	0.11	V
		$I_O = 1.1$ mA; $V_{CC} = 1.1$ V	-	-	$0.33 \times V_{CC}$	V
		$I_O = 1.7$ mA; $V_{CC} = 1.4$ V	-	-	0.41	V
		$I_O = 1.9$ mA; $V_{CC} = 1.65$ V	-	-	0.39	V
		$I_O = 2.3$ mA; $V_{CC} = 2.3$ V	-	-	0.36	V
		$I_O = 3.1$ mA; $V_{CC} = 2.3$ V	-	-	0.50	V
		$I_O = 2.7$ mA; $V_{CC} = 3.0$ V	-	-	0.36	V
		$I_O = 4.0$ mA; $V_{CC} = 3.0$ V	-	-	0.50	V
I_I	input leakage current	$V_I = \text{GND}$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	± 0.75	μ A
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	± 0.75	μ A
I_{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	± 0.75	μ A

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
ΔI_{OFF}	additional power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	± 0.75	μA
I_{CC}	supply current	$V_I = GND$ or V_{CC} ; $I_O = 0$ A; $V_{CC} = 0.8$ V to 3.6 V	-	-	1.4	μA
ΔI_{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1] -	-	75	μA
		$\overline{OE}$ input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1] -	-	180	μA
		all inputs; $V_I = GND$ to 3.6 V; $\overline{OE} = V_{CC}$; $V_{CC} = 0.8$ V to 3.6 V	[2] -	-	1	μA

[1] One input at $V_{CC} - 0.6$ V, other input at V_{CC} or GND.[2] To show I_{CC} remains very low when the input-disable feature is enabled.

11. Dynamic characteristics

Table 8. Dynamic characteristicsVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 10](#)

Symbol	Parameter	Conditions	Min	Typ [1]	Max	Unit
$T_{amb} = 25$ °C; $C_L = 5$ pF						
t_{pd}	propagation delay	A to Y; see Figure 8	[2]			
		$V_{CC} = 0.8$ V	-	20.6	-	ns
		$V_{CC} = 1.1$ V to 1.3 V	2.8	5.5	10.5	ns
		$V_{CC} = 1.4$ V to 1.6 V	2.2	3.9	6.1	ns
		$V_{CC} = 1.65$ V to 1.95 V	1.9	3.2	4.8	ns
		$V_{CC} = 2.3$ V to 2.7 V	1.6	2.6	3.6	ns
		$V_{CC} = 3.0$ V to 3.6 V	1.4	2.4	3.1	ns
t_{en}	enable time	$\overline{OE}$ to Y; see Figure 9	[3]			
		$V_{CC} = 0.8$ V	-	69.9	-	ns
		$V_{CC} = 1.1$ V to 1.3 V	3.1	6.1	11.8	ns
		$V_{CC} = 1.4$ V to 1.6 V	2.5	4.2	6.6	ns
		$V_{CC} = 1.65$ V to 1.95 V	2.1	3.4	5.1	ns
		$V_{CC} = 2.3$ V to 2.7 V	1.8	2.6	3.7	ns
		$V_{CC} = 3.0$ V to 3.6 V	1.7	2.4	3.1	ns
t_{dis}	disable time	$\overline{OE}$ to Y; see Figure 9	[4]			
		$V_{CC} = 0.8$ V	-	14.3	-	ns
		$V_{CC} = 1.1$ V to 1.3 V	2.7	4.3	6.5	ns
		$V_{CC} = 1.4$ V to 1.6 V	2.1	3.2	4.4	ns
		$V_{CC} = 1.65$ V to 1.95 V	2.0	3.0	4.3	ns
		$V_{CC} = 2.3$ V to 2.7 V	1.4	2.2	2.9	ns
		$V_{CC} = 3.0$ V to 3.6 V	1.7	2.5	3.2	ns

Table 8. Dynamic characteristics ...continuedVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 10](#)

Symbol	Parameter	Conditions	Min	Typ [1]	Max	Unit
T _{amb} = 25 °C; C _L = 10 pF						
t _{pd}	propagation delay	A to Y; see Figure 8 [2]				
		V _{CC} = 0.8 V	-	24.0	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.2	6.4	12.3	ns
		V _{CC} = 1.4 V to 1.6 V	2.1	4.5	7.3	ns
		V _{CC} = 1.65 V to 1.95 V	1.9	3.8	5.5	ns
		V _{CC} = 2.3 V to 2.7 V	2.1	3.2	4.2	ns
		V _{CC} = 3.0 V to 3.6 V	1.8	3.0	3.8	ns
t _{en}	enable time	$\overline{\text{OE}}$ to Y; see Figure 9 [3]				
		V _{CC} = 0.8 V	-	73.7	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.6	6.9	13.5	ns
		V _{CC} = 1.4 V to 1.6 V	2.3	4.8	7.7	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	3.9	5.8	ns
		V _{CC} = 2.3 V to 2.7 V	1.8	3.2	4.3	ns
		V _{CC} = 3.0 V to 3.6 V	1.7	3.0	3.9	ns
t _{dis}	disable time	$\overline{\text{OE}}$ to Y; see Figure 9 [4]				
		V _{CC} = 0.8 V	-	32.7	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.4	5.4	7.9	ns
		V _{CC} = 1.4 V to 1.6 V	2.2	4.1	5.5	ns
		V _{CC} = 1.65 V to 1.95 V	2.2	4.2	5.6	ns
		V _{CC} = 2.3 V to 2.7 V	1.7	3.0	3.8	ns
		V _{CC} = 3.0 V to 3.6 V	2.1	3.8	4.8	ns
T _{amb} = 25 °C; C _L = 15 pF						
t _{pd}	propagation delay	A to Y; see Figure 8 [2]				
		V _{CC} = 0.8 V	-	27.4	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.6	7.2	14.1	ns
		V _{CC} = 1.4 V to 1.6 V	3.0	5.1	8.1	ns
		V _{CC} = 1.65 V to 1.95 V	2.2	4.3	6.3	ns
		V _{CC} = 2.3 V to 2.7 V	2.0	3.7	4.9	ns
		V _{CC} = 3.0 V to 3.6 V	2.0	3.5	4.4	ns
t _{en}	enable time	$\overline{\text{OE}}$ to Y; see Figure 9 [3]				
		V _{CC} = 0.8 V	-	77.5	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.0	7.7	15.2	ns
		V _{CC} = 1.4 V to 1.6 V	3.0	5.3	8.4	ns
		V _{CC} = 1.65 V to 1.95 V	2.3	4.4	6.5	ns
		V _{CC} = 2.3 V to 2.7 V	2.1	3.6	5.0	ns
		V _{CC} = 3.0 V to 3.6 V	2.0	3.5	4.5	ns

Table 8. Dynamic characteristics ...continuedVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 10](#)

Symbol	Parameter	Conditions	Min	Typ ^[1]	Max	Unit
t _{dis}	disable time	$\overline{\text{OE}}$ to Y; see Figure 9 ^[4]				
		V _{CC} = 0.8 V	-	60.8	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.3	6.5	9.2	ns
		V _{CC} = 1.4 V to 1.6 V	3.0	5.0	6.5	ns
		V _{CC} = 1.65 V to 1.95 V	3.0	5.3	6.6	ns
		V _{CC} = 2.3 V to 2.7 V	2.1	3.8	4.9	ns
		V _{CC} = 3.0 V to 3.6 V	2.9	5.0	6.2	ns
T_{amb} = 25 °C; C_L = 30 pF						
t _{pd}	propagation delay	A to Y; see Figure 8 ^[2]				
		V _{CC} = 0.8 V	-	37.4	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.8	9.5	19.0	ns
		V _{CC} = 1.4 V to 1.6 V	4.0	6.7	10.8	ns
		V _{CC} = 1.65 V to 1.95 V	2.9	5.6	8.4	ns
		V _{CC} = 2.3 V to 2.7 V	2.7	4.8	6.3	ns
		V _{CC} = 3.0 V to 3.6 V	2.7	4.6	5.8	ns
t _{en}	enable time	$\overline{\text{OE}}$ to Y; see Figure 9 ^[3]				
		V _{CC} = 0.8 V	-	88.9	-	ns
		V _{CC} = 1.1 V to 1.3 V	5.2	9.9	19.8	ns
		V _{CC} = 1.4 V to 1.6 V	4.0	6.8	10.8	ns
		V _{CC} = 1.65 V to 1.95 V	3.0	5.6	8.5	ns
		V _{CC} = 2.3 V to 2.7 V	2.7	4.8	6.5	ns
		V _{CC} = 3.0 V to 3.6 V	2.7	4.6	6.0	ns
t _{dis}	disable time	$\overline{\text{OE}}$ to Y; see Figure 9 ^[4]				
		V _{CC} = 0.8 V	-	49.9	-	ns
		V _{CC} = 1.1 V to 1.3 V	6.0	9.9	13.3	ns
		V _{CC} = 1.4 V to 1.6 V	4.4	7.7	9.6	ns
		V _{CC} = 1.65 V to 1.95 V	5.1	8.7	11.1	ns
		V _{CC} = 2.3 V to 2.7 V	3.6	6.2	7.4	ns
		V _{CC} = 3.0 V to 3.6 V	5.2	8.7	10.5	ns

Table 8. Dynamic characteristics ...continuedVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 10](#)

Symbol	Parameter	Conditions	Min	Typ ^[1]	Max	Unit
T_{amb} = 25 °C						
C _{PD}	power dissipation capacitance	f = 1 MHz; V _I = GND to V _{CC} ^[5]				
		output enabled				
		V _{CC} = 0.8 V	-	2.7	-	pF
		V _{CC} = 1.1 V to 1.3 V	-	2.8	-	pF
		V _{CC} = 1.4 V to 1.6 V	-	2.9	-	pF
		V _{CC} = 1.65 V to 1.95 V	-	3.0	-	pF
		V _{CC} = 2.3 V to 2.7 V	-	3.6	-	pF
		V _{CC} = 3.0 V to 3.6 V	-	4.2	-	pF

[1] All typical values are measured at nominal V_{CC}.[2] t_{pd} is the same as t_{PLH} and t_{PHL}.[3] t_{en} is the same as t_{PZH} and t_{PZL}.[4] t_{dis} is the same as t_{PHZ} and t_{PLZ}.[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$$
 where:
f_i = input frequency in MHz;f_o = output frequency in MHz;C_L = output load capacitance in pF;V_{CC} = supply voltage in V;

N = number of inputs switching;

Σ(C_L × V_{CC}² × f_o) = sum of the outputs.**Table 9. Dynamic characteristics**Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 10](#)

Symbol	Parameter	Conditions	−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Max	Min	Max	
C _L = 5 pF							
t _{pd}	propagation delay	A to Y; see Figure 8	[1]				
		V _{CC} = 1.1 V to 1.3 V	2.5	11.7	2.5	12.9	ns
		V _{CC} = 1.4 V to 1.6 V	2.0	7.3	2.0	8.1	ns
		V _{CC} = 1.65 V to 1.95 V	1.7	6.1	1.7	6.7	ns
		V _{CC} = 2.3 V to 2.7 V	1.4	4.3	1.4	4.9	ns
		V _{CC} = 3.0 V to 3.6 V	1.2	3.9	1.2	4.4	ns
t _{en}	enable time	OE to Y; see Figure 9	[2]				
		V _{CC} = 1.1 V to 1.3 V	2.9	13.9	2.9	15.4	ns
		V _{CC} = 1.4 V to 1.6 V	2.3	7.7	2.3	8.3	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	6.2	2.0	6.8	ns
		V _{CC} = 2.3 V to 2.7 V	1.7	4.5	1.7	5.0	ns
		V _{CC} = 3.0 V to 3.6 V	1.7	3.5	1.7	3.9	ns

Table 9. Dynamic characteristics ...continuedVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 10](#)

Symbol	Parameter	Conditions	–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Max	Min	Max	
t _{dis}	disable time	$\overline{\text{OE}}$ to Y; see Figure 9 [3]					
		V _{CC} = 1.1 V to 1.3 V	2.7	7.3	2.7	8.2	ns
		V _{CC} = 1.4 V to 1.6 V	2.1	5.1	2.1	5.7	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	5.0	2.0	5.7	ns
		V _{CC} = 2.3 V to 2.7 V	1.4	3.3	1.4	4.1	ns
		V _{CC} = 3.0 V to 3.6 V	1.7	3.4	1.7	3.9	ns
C _L = 10 pF							
t _{pd}	propagation delay	A to Y; see Figure 8 [1]					
		V _{CC} = 1.1 V to 1.3 V	3.0	13.8	3.0	15.2	ns
		V _{CC} = 1.4 V to 1.6 V	1.9	8.5	1.9	9.4	ns
		V _{CC} = 1.65 V to 1.95 V	1.7	6.8	1.7	7.6	ns
		V _{CC} = 2.3 V to 2.7 V	1.6	5.3	1.6	5.9	ns
		V _{CC} = 3.0 V to 3.6 V	1.6	4.6	1.6	5.2	ns
t _{en}	enable time	$\overline{\text{OE}}$ to Y; see Figure 9 [2]					
		V _{CC} = 1.1 V to 1.3 V	3.4	15.8	3.4	17.5	ns
		V _{CC} = 1.4 V to 1.6 V	2.2	8.6	2.2	9.4	ns
		V _{CC} = 1.65 V to 1.95 V	1.9	6.8	1.9	7.4	ns
		V _{CC} = 2.3 V to 2.7 V	1.7	5.3	1.7	5.9	ns
		V _{CC} = 3.0 V to 3.6 V	1.7	4.3	1.7	4.8	ns
t _{dis}	disable time	$\overline{\text{OE}}$ to Y; see Figure 9 [3]					
		V _{CC} = 1.1 V to 1.3 V	3.4	8.8	3.4	9.9	ns
		V _{CC} = 1.4 V to 1.6 V	2.2	6.2	2.2	7.1	ns
		V _{CC} = 1.65 V to 1.95 V	1.9	6.3	1.9	7.1	ns
		V _{CC} = 2.3 V to 2.7 V	1.7	4.5	1.7	5.1	ns
		V _{CC} = 3.0 V to 3.6 V	1.7	5.0	1.7	5.6	ns
C _L = 15 pF							
t _{pd}	propagation delay	A to Y; see Figure 8 [1]					
		V _{CC} = 1.1 V to 1.3 V	3.3	15.8	3.3	17.5	ns
		V _{CC} = 1.4 V to 1.6 V	2.5	9.8	2.5	10.9	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	7.9	2.0	8.8	ns
		V _{CC} = 2.3 V to 2.7 V	1.8	6.0	1.8	6.7	ns
		V _{CC} = 3.0 V to 3.6 V	1.8	5.4	1.8	6.1	ns
t _{en}	enable time	$\overline{\text{OE}}$ to Y; see Figure 9 [2]					
		V _{CC} = 1.1 V to 1.3 V	3.7	17.6	3.7	19.6	ns
		V _{CC} = 1.4 V to 1.6 V	2.5	9.8	2.5	10.7	ns
		V _{CC} = 1.65 V to 1.95 V	2.1	7.7	2.1	8.5	ns
		V _{CC} = 2.3 V to 2.7 V	2.0	6.1	2.0	6.8	ns
		V _{CC} = 3.0 V to 3.6 V	1.9	4.9	1.9	5.5	ns

Table 9. Dynamic characteristics ...continuedVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 10](#)

Symbol	Parameter	Conditions	–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Max	Min	Max	
t _{dis}	disable time	$\overline{\text{OE}}$ to Y; see Figure 9 [3]					
		V _{CC} = 1.1 V to 1.3 V	3.7	10.3	3.7	11.6	ns
		V _{CC} = 1.4 V to 1.6 V	2.5	7.4	2.5	8.4	ns
		V _{CC} = 1.65 V to 1.95 V	2.1	7.4	2.1	8.9	ns
		V _{CC} = 2.3 V to 2.7 V	2.0	5.1	2.0	6.4	ns
		V _{CC} = 3.0 V to 3.6 V	1.9	6.6	1.9	7.4	ns
C _L = 30 pF							
t _{pd}	propagation delay	A to Y; see Figure 8 [1]					
		V _{CC} = 1.1 V to 1.3 V	4.4	21.6	4.4	24.0	ns
		V _{CC} = 1.4 V to 1.6 V	3.0	13.0	3.0	14.5	ns
		V _{CC} = 1.65 V to 1.95 V	2.6	10.3	2.6	11.5	ns
		V _{CC} = 2.3 V to 2.7 V	2.5	7.8	2.5	8.7	ns
		V _{CC} = 3.0 V to 3.6 V	2.5	7.5	2.5	8.3	ns
t _{en}	enable time	$\overline{\text{OE}}$ to Y; see Figure 9 [2]					
		V _{CC} = 1.1 V to 1.3 V	4.8	22.8	4.8	25.3	ns
		V _{CC} = 1.4 V to 1.6 V	3.1	12.6	3.1	14.1	ns
		V _{CC} = 1.65 V to 1.95 V	2.8	10.2	2.8	11.3	ns
		V _{CC} = 2.3 V to 2.7 V	2.6	7.8	2.6	8.8	ns
		V _{CC} = 3.0 V to 3.6 V	2.6	6.9	2.6	7.7	ns
t _{dis}	disable time	$\overline{\text{OE}}$ to Y; see Figure 9 [3]					
		V _{CC} = 1.1 V to 1.3 V	4.8	14.8	4.8	16.5	ns
		V _{CC} = 1.4 V to 1.6 V	3.1	10.7	3.1	12.1	ns
		V _{CC} = 1.65 V to 1.95 V	2.8	12.4	2.8	13.8	ns
		V _{CC} = 2.3 V to 2.7 V	2.6	8.6	2.6	9.6	ns
		V _{CC} = 3.0 V to 3.6 V	2.6	10.8	2.6	13.1	ns

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .[2] t_{en} is the same as t_{PZH} and t_{PZL} .[3] t_{dis} is the same as t_{PHZ} and t_{PLZ} .

12. Waveforms

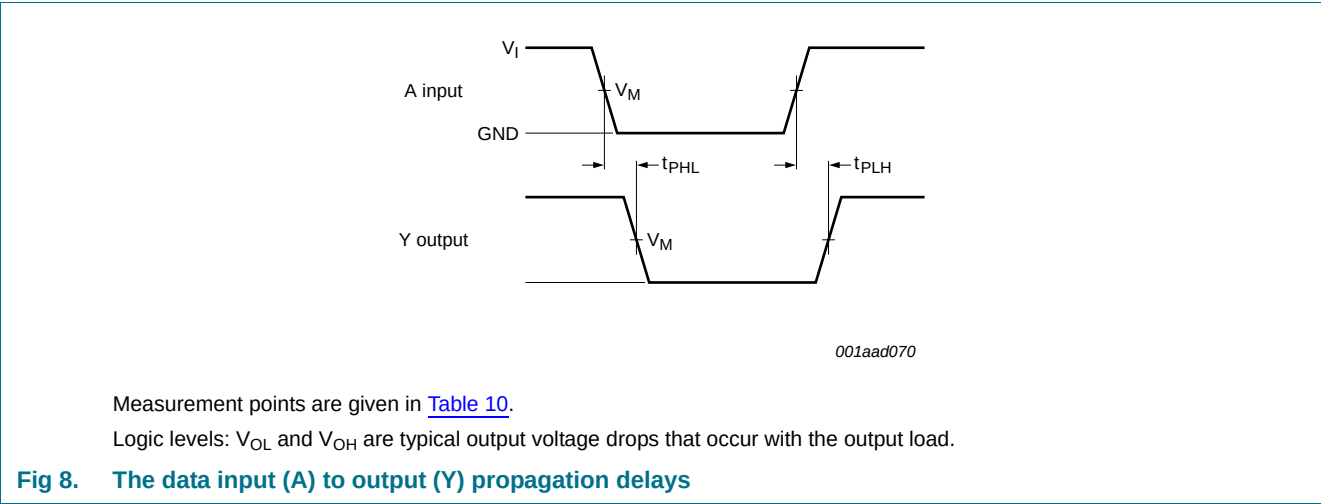


Table 10. Measurement points

Supply voltage	Output	Input		
V_{CC}	V_M	V_M	V_I	$t_r = t_f$
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V_{CC}	$\leq 3.0 \text{ ns}$

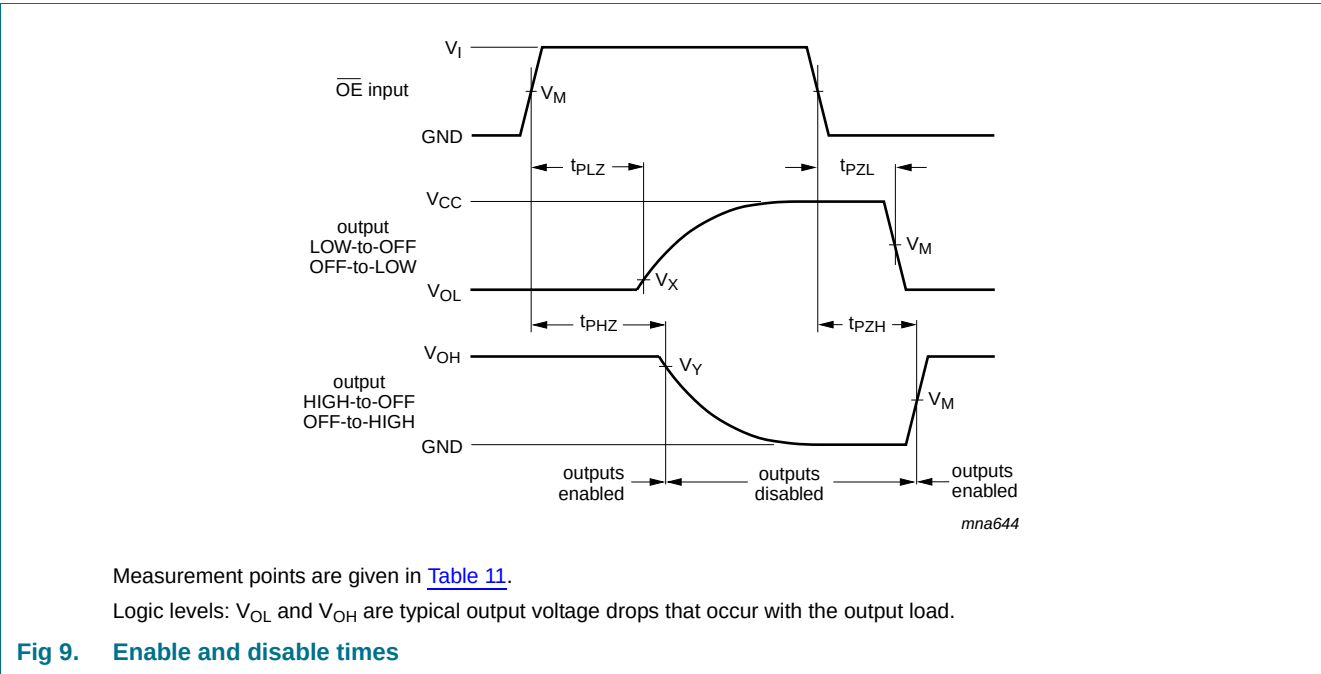
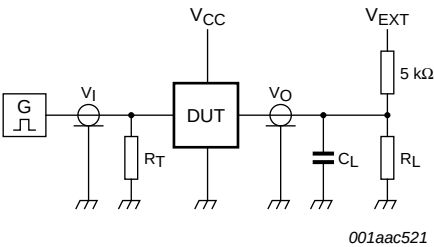


Table 11. Measurement points

Supply voltage	Input	Output		
V _{CC}	V _M	V _M	V _X	V _Y
0.8 V to 1.6 V	0.5 × V _{CC}	0.5 × V _{CC}	V _{OL} + 0.1 V	V _{OH} − 0.1 V
1.65 V to 2.7 V	0.5 × V _{CC}	0.5 × V _{CC}	V _{OL} + 0.15 V	V _{OH} − 0.15 V
3.0 V to 3.6 V	0.5 × V _{CC}	0.5 × V _{CC}	V _{OL} + 0.3 V	V _{OH} − 0.3 V



Test data is given in [Table 12](#).
Definitions for test circuit:
R_L = Load resistance.
C_L = Load capacitance including jig and probe capacitance.
R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.
V_{EXT} = External voltage for measuring switching times.

Fig 10. Test circuit for measuring switching times

Table 12. Test data

Supply voltage	Load		V _{EXT}			
V _{CC}	C _L	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}	
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	2 × V _{CC}	

[1] For measuring enable and disable times R_L = 5 kΩ, for measuring propagation delays, setup and hold times and pulse width R_L = 1 MΩ.

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mmSOT353-1

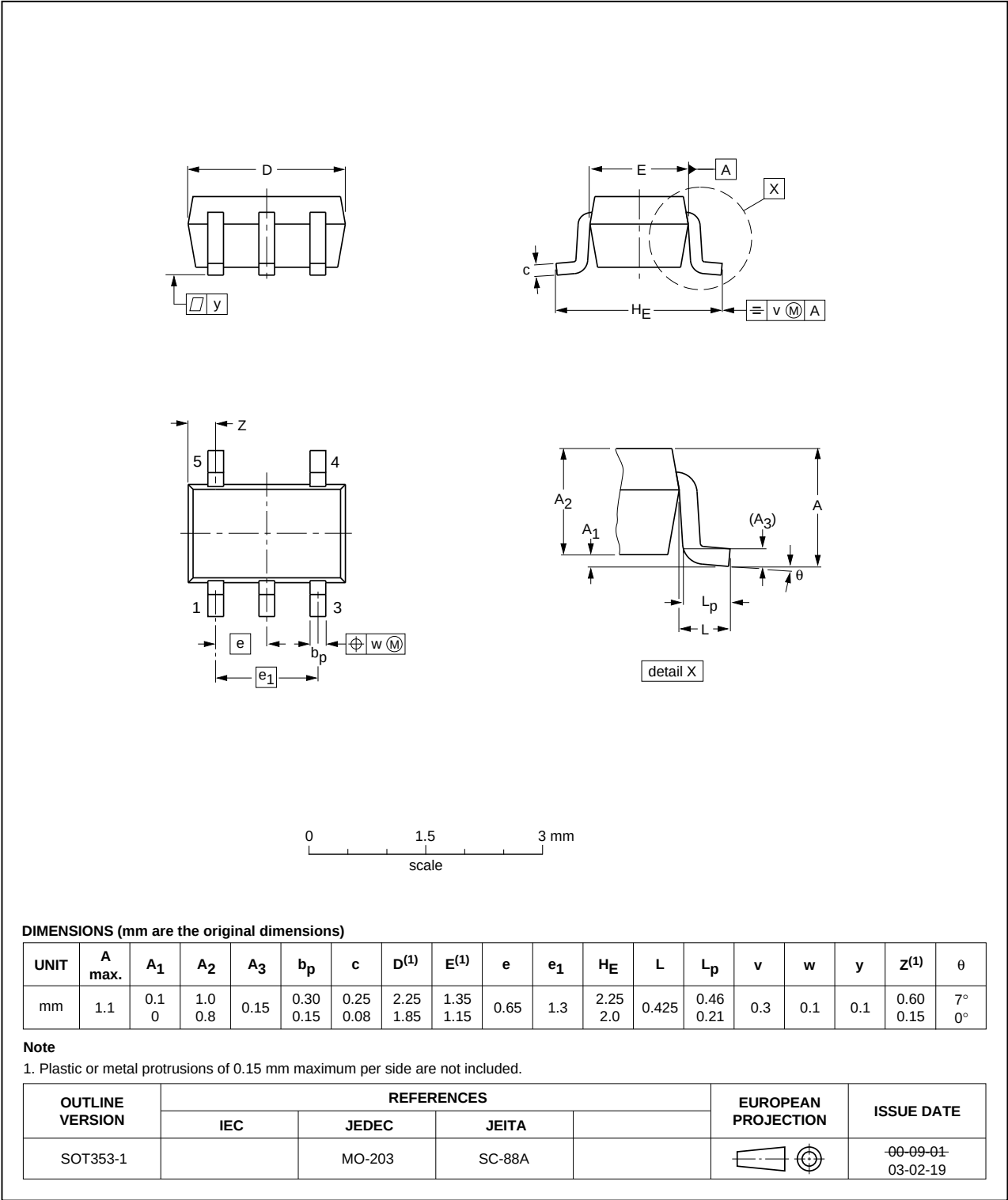


Fig 11. Package outline SOT353-1 (TSSOP5)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886

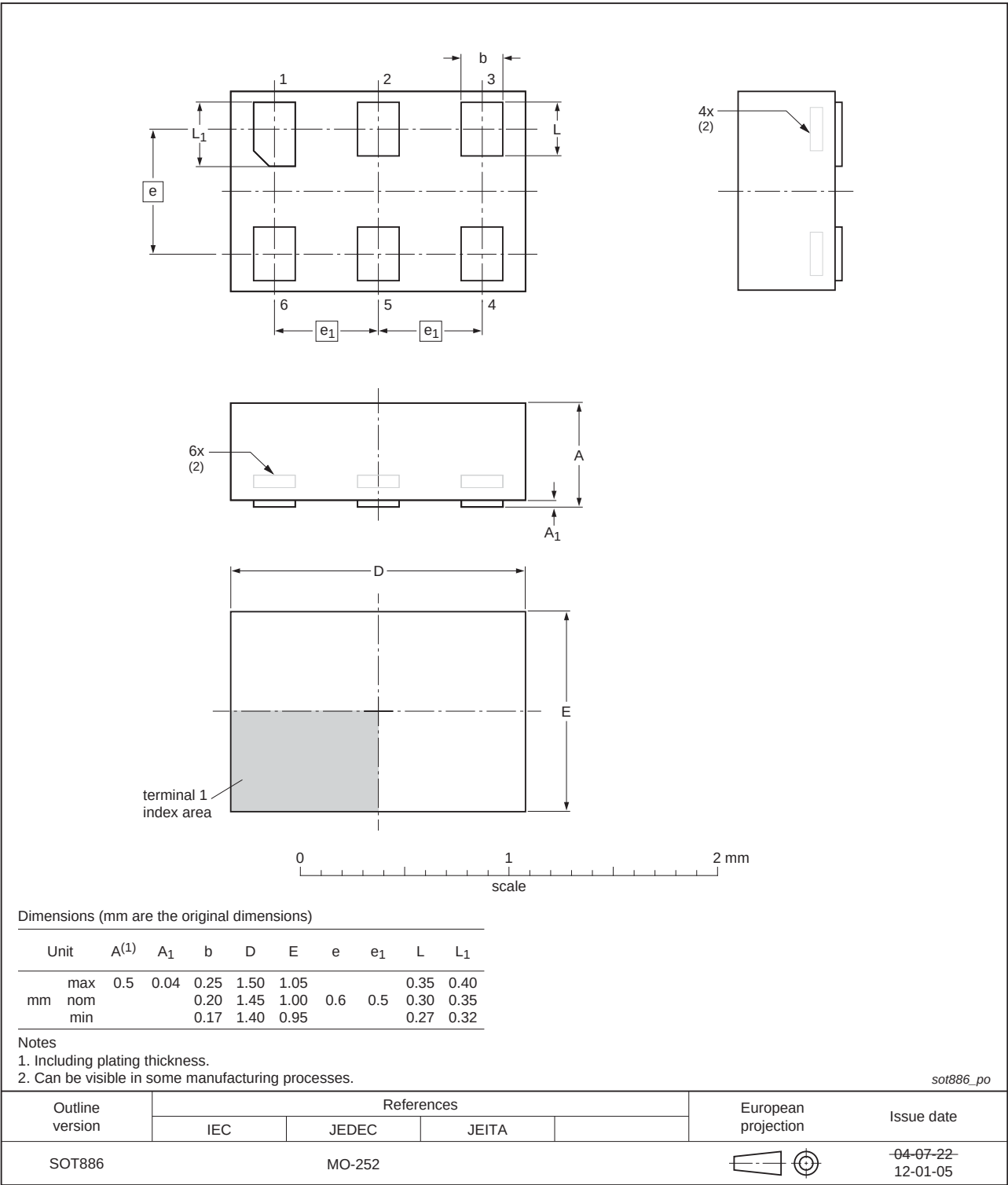


Fig 12. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

SOT891

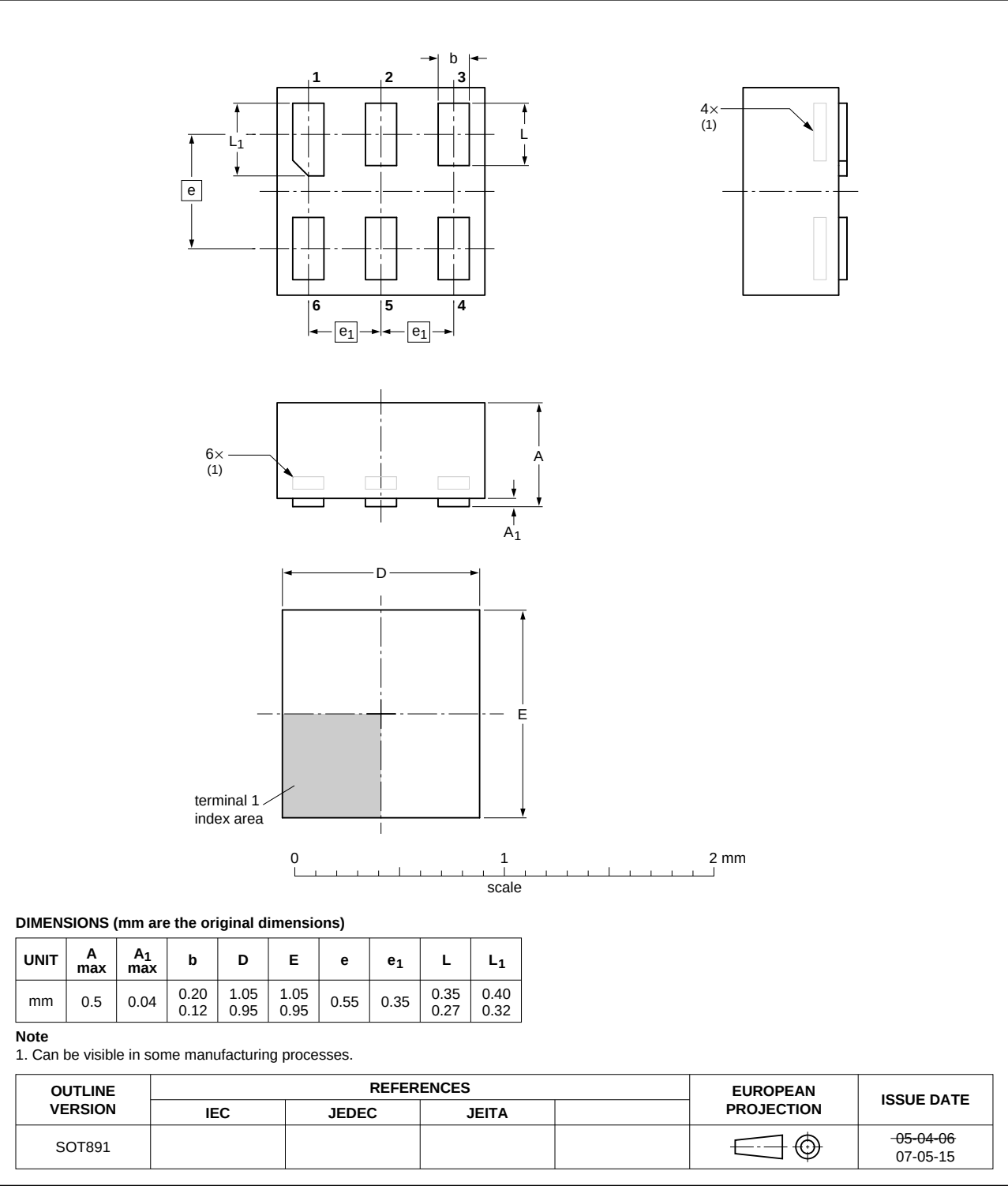


Fig 13. Package outline SOT891 (XSON6)

XSON6: extremely thin small outline package; no leads;
6 terminals; body 0.9 x 1.0 x 0.35 mm

SOT1115

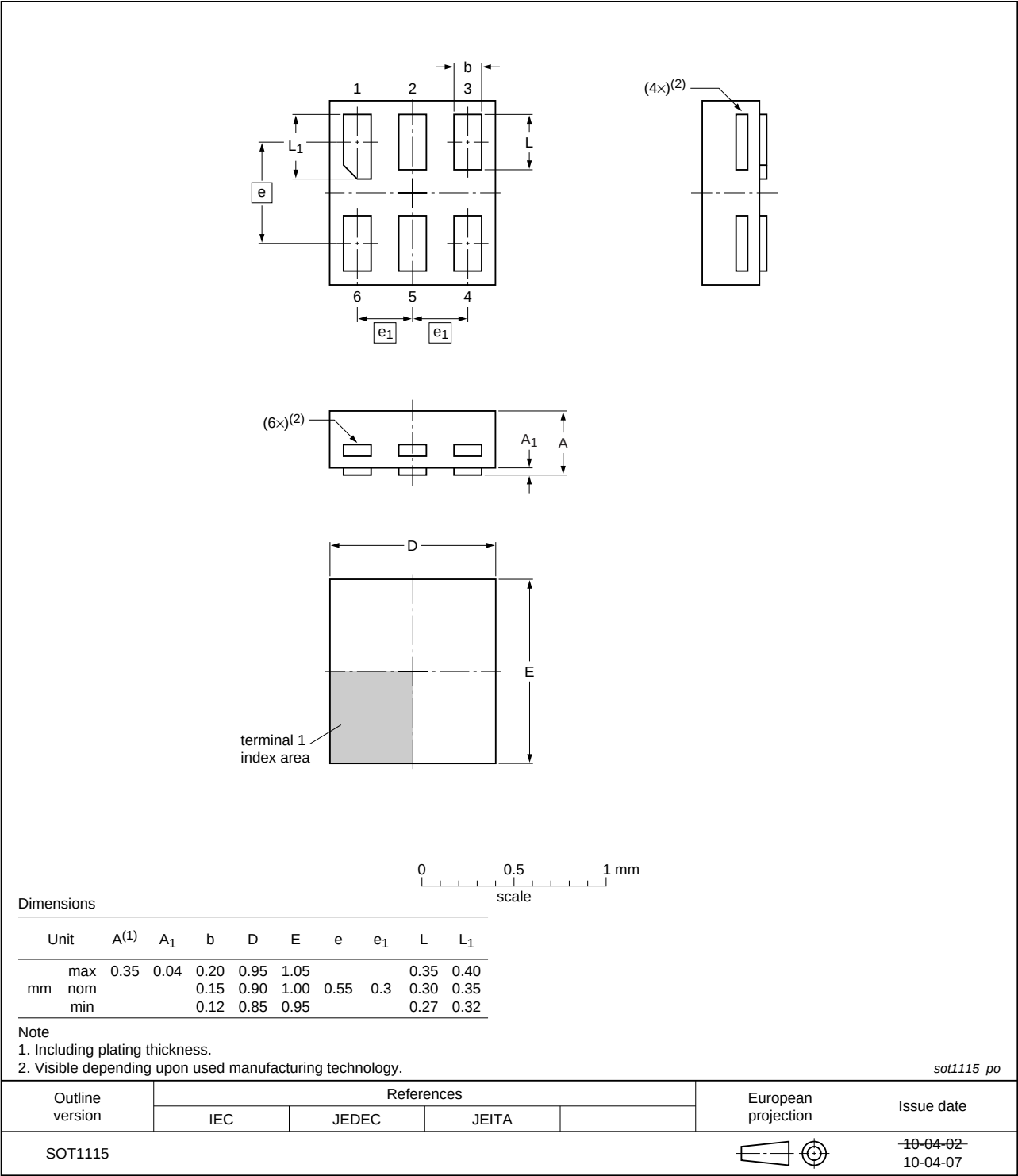
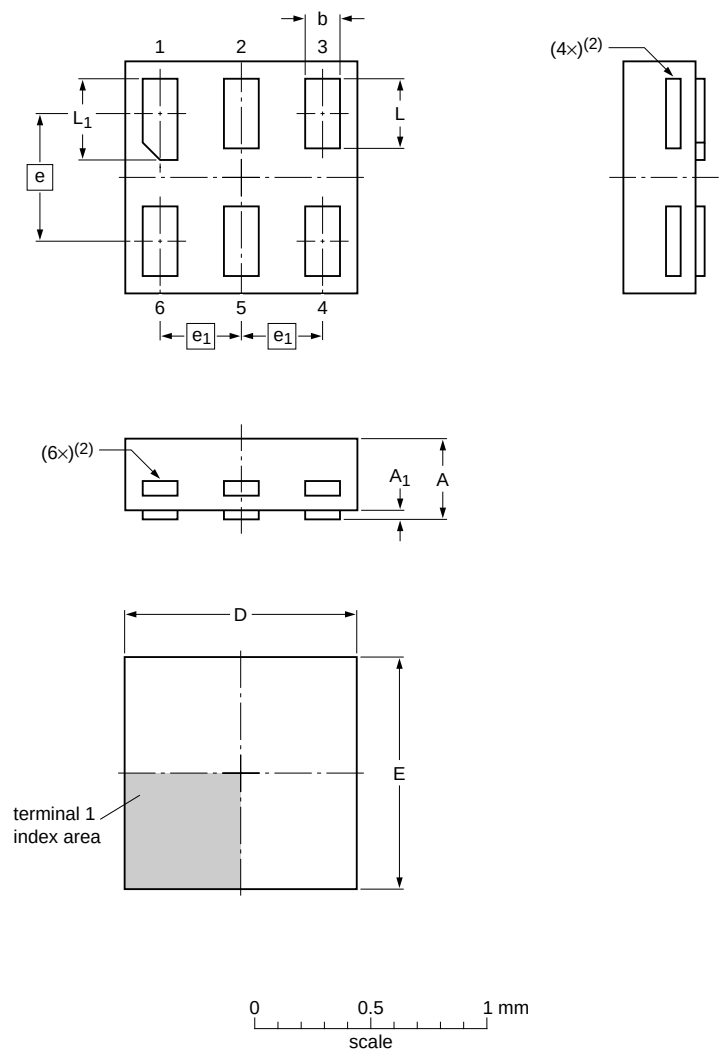


Fig 14. Package outline SOT1115 (XSON6)

XSON6: extremely thin small outline package; no leads;
6 terminals; body 1.0 x 1.0 x 0.35 mm

SOT1202



Dimensions

Unit	A ⁽¹⁾	A ₁	b	D	E	e	e ₁	L	L ₁
mm	max	0.35	0.04	0.20	1.05	1.05		0.35	0.40
	nom			0.15	1.00	1.00	0.55	0.30	0.35
	min			0.12	0.95	0.95		0.27	0.32

Note

- 1. Including plating thickness.
- 2. Visible depending upon used manufacturing technology.

sot1202_po

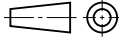
Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1202						10-04-02 10-04-06

Fig 15. Package outline SOT1202 (XSON6)

X2SON5: plastic thermal enhanced extremely thin small outline package; no leads;
5 terminals; body 0.8 x 0.8 x 0.35 mm

SOT1226

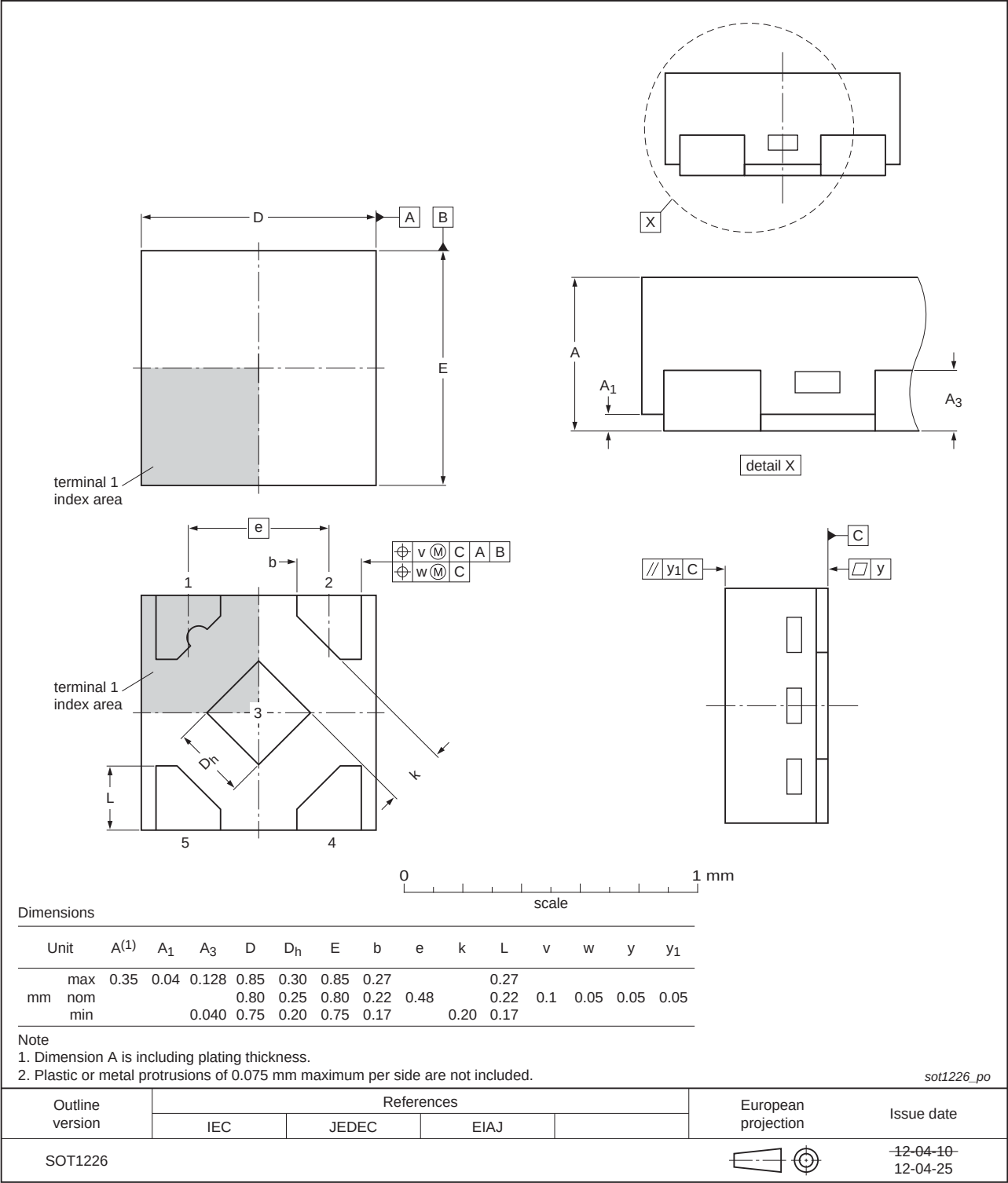


Fig 16. Package outline SOT1226 (X2SON5)

14. Abbreviations

Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

15. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G125 v.6	20120815	Product data sheet	-	74AUP1G125 v.5
Modifications:	• Errata in general description corrected			
74AUP1G125 v.5	20120731	Product data sheet	-	74AUP1G125 v.4
Modifications:	• Added type number 74AUP1G125GX (SOT1226) • Package outline drawing of SOT886 (Figure 12) modified.			
74AUP1G125 v.4	20111129	Product data sheet	-	74AUP1G125 v.3
74AUP1G125 v.3	20100901	Product data sheet	-	74AUP1G125 v.2
74AUP1G125 v.2	20060630	Product data sheet	-	74AUP1G125 v.1
74AUP1G125 v.1	20050718	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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18. Contents

1	General description	1
2	Features and benefits	1
3	Ordering information	2
4	Marking	2
5	Functional diagram	2
6	Pinning information	3
6.1	Pinning	3
6.2	Pin description	3
7	Functional description	4
8	Limiting values	4
9	Recommended operating conditions	4
10	Static characteristics	5
11	Dynamic characteristics	8
12	Waveforms	14
13	Package outline	16
14	Abbreviations	22
15	Revision history	22
16	Legal information	23
16.1	Data sheet status	23
16.2	Definitions	23
16.3	Disclaimers	23
16.4	Trademarks	24
17	Contact information	24
18	Contents	25

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